ABSTRACT

A vapor growth device which is constituted as a single-wafer type and has a gas introducing port through which a material gas is led into a reaction vessel. A dam member is disposed around a susceptor, and the material gas from the gas introducing port hits the outer peripheral surface of the dam ring and rides on an upper surface side, and then is allowed to flow along the main surface of a silicon single-crystal substrate placed on the susceptor. Guide plates for dividing the flow in the width direction of the material gas are disposed on the upper surface of the dam member. Accordingly, a vapor growth device capable of controlling the flow rate of material gas flowing on a silicon single-crystal substrate, and a production method for an epitaxial wafer using it are provided.